

Silicon PNP Darlington Power Transistors

2SB1626

DESCRIPTION

- With TO-220F package
- Complement to type 2SD2495

APPLICATIONS

- For audio, series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

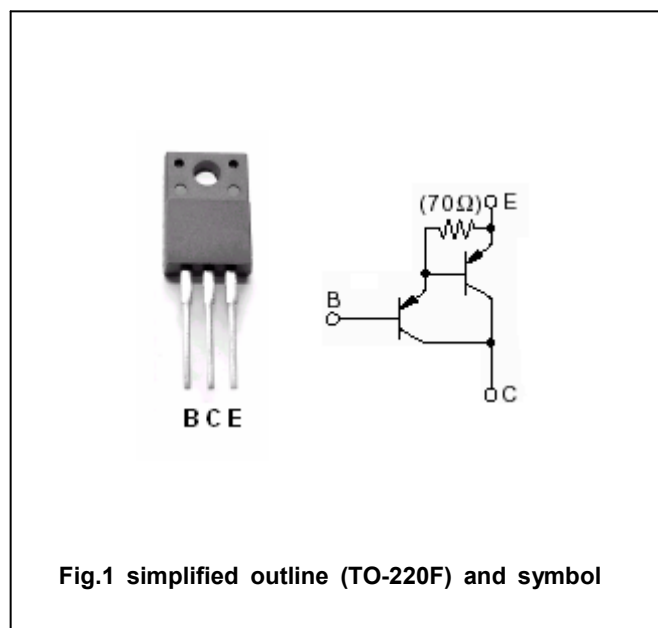


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-110	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-6	A
I_B	Base current		-1	A
P_C	Collector dissipation	$T_C=25^\circ\text{C}$	30	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; I_B=0$	-110			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A; I_B=-5mA$			-2.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-5A; I_B=-5mA$			-3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-110V; I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-5A; V_{CE}=-4V$	5000			
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-12V$		100		MHz
C_{OB}	Collector output capacitance	$f=1MHz; V_{CB}=-10V$		110		pF

Switching times

t_{on}	Turn-on time	$I_C=-5A; I_{B1}=-I_{B2}=-5mA$ $V_{CC}=30V, R_L=6\Omega$		1.1		μs
t_s	Storage time			3.2		μs
t_f	Fall time			1.1		μs

◆ h_{FE} Classifications

O	p	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

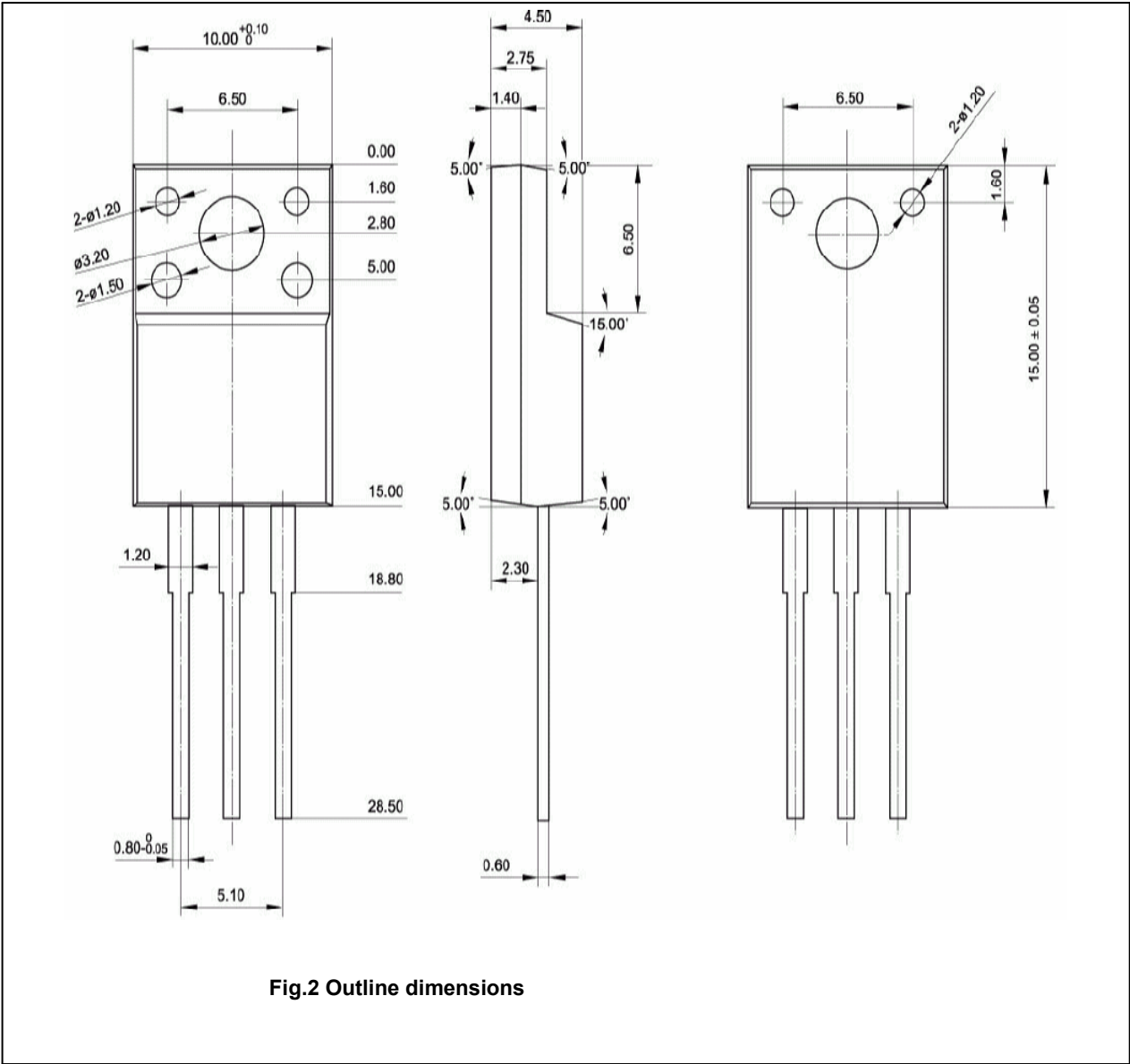


Fig.2 Outline dimensions